

# SI2310-TP Datasheet

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DiGi Electronics Part Number

SI2310-TP-DG

Manufacturer

Micro Commercial Co

Manufacturer Product Number

SI2310-TP

Description

MOSFET N-CH 60V 3A SOT23

**Detailed Description** 

N-Channel 60 V 3A (Ta) 350mW (Ta) Surface Mount

SOT-23

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## **Purchase and inquiry**

| Manufacturer Product Number:            | Manufacturer:                           |
|---|---|
| SI2310-TP                               | Micro Commercial Co                     |
| Series:                                 | Product Status:                         |
|   | Active                                  |
| FET Type:                               | Technology:                             |
| N-Channel                               | MOSFET (Metal Oxide)                    |
| Drain to Source Voltage (Vdss):         | Current - Continuous Drain (Id) @ 25°C: |
| 60 V                                    | 3A (Ta)                                 |
| Drive Voltage (Max Rds On, Min Rds On): | Rds On (Max) @ Id, Vgs:                 |
| 10V                                     | 125mOhm @ 3A, 4.5V                      |
| Vgs(th) (Max) @ ld:                     | Gate Charge (Qg) (Max) @ Vgs:           |
| 2V @ 250μA                              | 6 nC @ 4.5 V                            |
| Vgs (Max):                              | Input Capacitance (Ciss) (Max) @ Vds:   |
| ±20V                                    | 247 pF @ 30 V                           |
| FET Feature:                            | Power Dissipation (Max):                |
| -                                       | 350mW (Ta)                              |
| Operating Temperature:                  | Mounting Type:                          |
| -55°C ~ 150°C (TJ)                      | Surface Mount                           |
| Supplier Device Package:                | Package / Case:                         |
| SOT-23                                  | TO-236-3, SC-59, SOT-23-3               |
| Base Product Number:                    |   |
| SI2310                                  |   |

## **Environmental & Export classification**

| RoHS Status:     | Moisture Sensitivity Level (MSL): |
|------------------|-----------------------------------|
| ROHS3 Compliant  | 1 (Unlimited)                     |
| REACH Status:    | ECCN:                             |
| REACH Unaffected | EAR99                             |
| HTSUS:           |                                   |
| 8541.21.0095     |                                   |



### **Features**

- Trench MV MOSFET Technology
- · Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

## **Maximum Ratings**

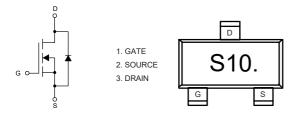
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 105°C/W Junction to Ambient<sup>(Note 2)</sup>

| Parameter                                | Symbol               | Rating           | Unit |   |  |
|--|----------------------|------------------|------|---|--|
| Drain-Source Voltage                     | V <sub>DS</sub>      | 60               | V    |   |  |
| Gate-Source Volltage                     | V <sub>GS</sub>      | ±20              | V    |   |  |
| Continuous Drain Current                 | T <sub>A</sub> =25°C |                  | 3    |   |  |
|  | T <sub>A</sub> =70°C | - I <sub>D</sub> | 2.4  | A |  |
| Pulsed Drain Current <sup>(Note 3)</sup> | I <sub>DM</sub>      | 12               | Α    |   |  |
| Total Power Dissipation (Note 4)         |                      | P <sub>D</sub>   | 1.2  | W |  |

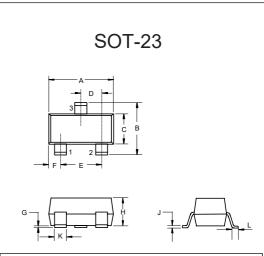
#### Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of  $R_{\theta JA}$  is measured with the device mounted on  $1 \text{in}^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A$  =25°C.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. P<sub>D</sub> is based on max. junction temperature, using junction-ambient thermal resistance.

## **Internal Structure and Marking Code**

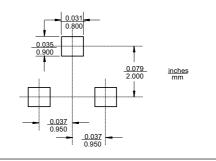


## **N-Channel MOSFET**



|       | DIMENSIONS |       |      |      |      |  |
|-------|------------|-------|------|------|------|--|
| DIM   | INCHES     |       | MM   |      | NOTE |  |
| DIIVI | MIN        | MAX   | MIN  | MAX  | NOIL |  |
| Α     | 0.110      | 0.120 | 2.80 | 3.04 |      |  |
| В     | 0.083      | 0.104 | 2.10 | 2.64 |      |  |
| С     | 0.047      | 0.055 | 1.20 | 1.40 |      |  |
| D     | 0.034      | 0.041 | 0.85 | 1.05 |      |  |
| Е     | 0.067      | 0.083 | 1.70 | 2.10 |      |  |
| F     | 0.018      | 0.024 | 0.45 | 0.60 |      |  |
| G     | 0.0004     | 0.006 | 0.01 | 0.15 |      |  |
| Н     | 0.035      | 0.043 | 0.90 | 1.10 |      |  |
| J     | 0.003      | 0.007 | 0.08 | 0.18 |      |  |
| K     | 0.012      | 0.020 | 0.30 | 0.51 |      |  |
| L     | 0.007      | 0.020 | 0.20 | 0.50 |      |  |

#### **Suggested Solder Pad Layout**





## Electrical Characteristics @ 25°C (Unless Otherwise Specified)

| Parameter                       | Symbol               | Test conditions  | Min | Тур | Max  | Unit |  |
|---------------------------------|----------------------|--|-----|-----|------|------|--|
| Static Characteristics          |                      |  |     | 1   |      | 1    |  |
| Drain-Source Breakdown Voltage  | V <sub>(BR)DSS</sub> | V <sub>GS</sub> =0V, I <sub>D</sub> =250μA               | 60  |     |      | V    |  |
| Gate-Threshold Voltage          | V <sub>GS(th)</sub>  | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA | 0.5 | 1.4 | 2.0  | V    |  |
| Gate-Body Leakage Current       | I <sub>GSS</sub>     | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V               |     |     | ±100 | nA   |  |
| Zero Gate Voltage Drain Current | I <sub>DSS</sub>     | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V                |     |     | 1    | μA   |  |
| Drain-Source On-Resistance      | R                    | V <sub>GS</sub> =10V, I <sub>D</sub> =3A                 |     | 63  | 105  | mΩ   |  |
| Dialii-Source On-Resistance     | R <sub>DS(on)</sub>  | V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A                |     | 70  | 125  |      |  |
| Forward Transconductance        | g <sub>FS</sub>      | $V_{DS}$ =5V, $I_{D}$ =3A                                |     | 8.5 |      | S    |  |
| Gate Resistance                 | R <sub>g</sub>       | f=1 MHz, Open drain                                      |     | 1.7 |      | Ω    |  |
| Diode Characteristics           | -                    |  | ,   |     | 1    |      |  |
| Continuous Body Diode Current   | Is                   |  |     |     | 3    | А    |  |
| Diode Forward Voltage           | V <sub>SD</sub>      | V <sub>GS</sub> =0V, I <sub>S</sub> =3A                  |     |     | 1.2  | V    |  |
| Reverse Recovery Time           | t <sub>rr</sub>      | I <sub>F</sub> =3A, dI <sub>F</sub> /dt=100A/µs          |     | 14  |      | ns   |  |
| Reverse Recovery Charge         | Q <sub>rr</sub>      | - 1;-3A, αιε/αι-100A/μ5                                  |     | 11  |      | nC   |  |
| Dynamic Characteristics         |                      |  |     |     |      |      |  |
| Input Capacitance               | C <sub>iss</sub>     |  |     | 546 |      |      |  |
| Output Capacitance              | C <sub>oss</sub>     | V <sub>DS</sub> =10V,V <sub>GS</sub> =0V,f=1MHz          |     | 45  |      | pF   |  |
| Reverse Transfer Capacitance    | C <sub>rss</sub>     |  |     | 35  |      | 1    |  |
| Total Gate Charge               | Qg                   |  |     | 10  |      |      |  |
| Gate-Source Charge              | $Q_{gs}$             | $V_{DS}$ =30V, $V_{GS}$ =10V, $I_{D}$ =3A                |     | 1.7 |      | nC   |  |
| Gate-Drain Charge               | $Q_{gd}$             |  |     | 2   |      |      |  |
| Turn-On Delay Time              | t <sub>d(on)</sub>   |  |     | 6   |      |      |  |
| Turn-On Rise Time               | t <sub>r</sub>       | V <sub>DD</sub> =30V,V <sub>GS</sub> =10V,               |     | 3   |      |      |  |
| Turn-Off Delay Time             | t <sub>d(off)</sub>  | $R_G=2.7\Omega$ , $I_D=2A$                               |     | 16  |      | ns   |  |
| Turn-Off Fall Time              | t <sub>f</sub>       |  |     | 2.5 |      |      |  |



## **Curve Characteristics**

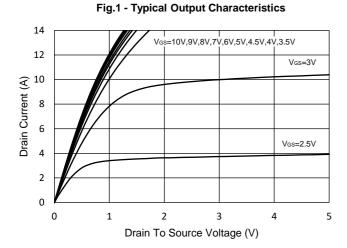


Fig.2 - Transfer Characteristic

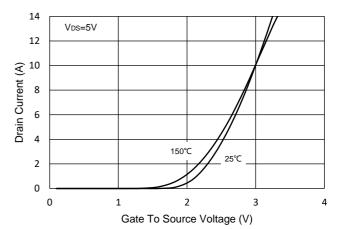


Fig.3 - R<sub>DS(ON)</sub> - V<sub>GS</sub>

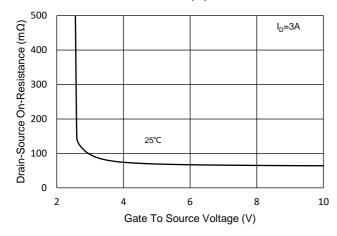


Fig.4 - R<sub>DS(ON)</sub> - I<sub>D</sub>

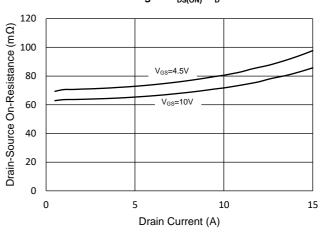


Fig.5 - Capacitance Characteristics

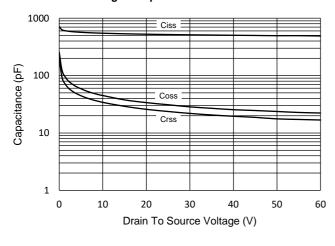
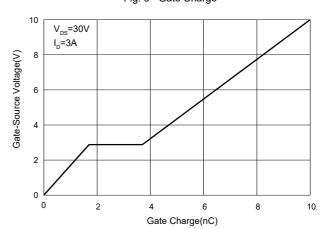


Fig. 6 - Gate Charge





1.4

## **Curve Characteristics**

Fig.7 - Normalized Threshold Voltage I<sub>D</sub>=250μA

VGS(th) - Threshold Voltage Normalized 1.2 1.0 0.8 0.6 0.4 0.2 25 75 -50 -25 0 50 100 125 150

T<sub>J</sub> - Junction Temperature(°C)

2.5 Vgs=10V ID= 3A Normalized On Resistance 2.0 1.0 0.0

25

50

T<sub>.1</sub> - Junction Temperature(°C)

75

100

125

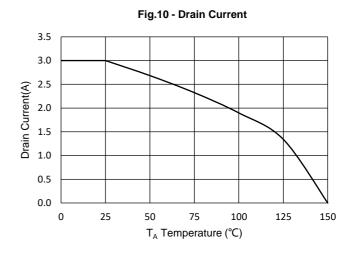
150

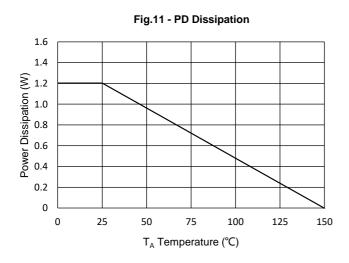
-50

-25

Fig.8 - Normalized On Resistance Characteristics

Fig.9 -  $I_S$  -  $V_{SD}$ 100 Vgs=0V Source Current (A) 10 150℃ 1 0.1 0.2 0.0 0.4 0.6 0.8 1.0 1.2 Source To Drain Voltage (V)







## **Curve Characteristics**

Fig.12 - Safe Operation Area

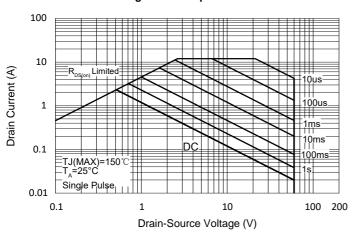
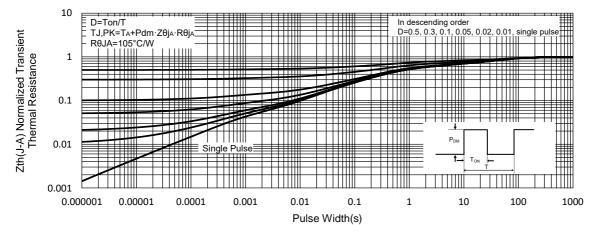


Fig.13 - Normalized Transient Thermal Impedance





## **Ordering Information**

| Device         | Packing              |  |  |
|----------------|----------------------|--|--|
| Part Number-TP | Tape&Reel:3Kpcs/Reel |  |  |

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